

Transistors

N-ch

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	10	μA	$V_{GS}=12V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	–	–	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.5	–	1.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	170	230	m Ω	$I_D=1.5A, V_{GS}=4.5V$
		–	180	245		$I_D=1.5A, V_{GS}=4.0V$
		–	260	360		$I_D=1.0A, V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	1.0	–	–	S	$I_D=1.0A, V_{DS}=10V$
Input capacitance	C_{iss}	–	80	–	pF	$V_{DS}=10V$
Output capacitance	C_{oss}	–	25	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	–	15	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	7	–	ns	$I_D=1A, V_{DD}\doteq 15V$
Rise time	t_r *	–	18	–	ns	$V_{GS}=4.5V$
Turn-off delay time	$t_{d(off)}$ *	–	15	–	ns	$R_L=15\Omega$
Fall time	t_f *	–	15	–	ns	$R_G=10\Omega$
Total gate charge	Q_g *	–	1.6	–	nC	$V_{DD}\doteq 15V, R_L=10\Omega$
Gate-source charge	Q_{gs} *	–	0.5	–	nC	$V_{GS}=4.5V, R_G=10\Omega$
Gate-drain charge	Q_{gd} *	–	0.9	–	nC	$I_D=1.5A$

*Pulsed

●Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD} *	–	–	1.2	V	$I_S=3.2A, V_{GS}=0V$

*Pulsed

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	–10	μA	$V_{GS} = -12V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	–20	–	–	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	–0.7	–	–2.0	V	$V_{DS} = -10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	155	215	m Ω	$I_D = -1.5A, V_{GS} = -4.5V$
		–	170	235		$I_D = -1.5A, V_{GS} = -4.0V$
		–	310	430		$I_D = -0.75A, V_{GS} = -2.5V$
Forward transfer admittance	$ Y_{fs} $ *	1.0	–	–	S	$I_D = -0.75A, V_{DS} = -10V$
Input capacitance	C_{iss}	–	270	–	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	–	40	–	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	–	35	–	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	10	–	ns	$I_D = -0.75A, V_{DD} = -15V$
Rise time	t_r *	–	12	–	ns	$V_{GS} = -4.5V$
Turn-off delay time	$t_{d(off)}$ *	–	45	–	ns	$R_L = 20\Omega$
Fall time	t_f *	–	20	–	ns	$R_G = 10\Omega$
Total gate charge	Q_g *	–	3.0	–	nC	$V_{DD} = -15V, R_L = 10\Omega$
Gate-source charge	Q_{gs} *	–	0.8	–	nC	$V_{GS} = -4.5V, R_G = 10\Omega$
Gate-drain charge	Q_{gd} *	–	0.85	–	nC	$I_D = -1.5A$

*Pulsed

●Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	–1.2	V	$I_S = -0.75A, V_{GS} = 0V$

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●Electrical characteristic curves

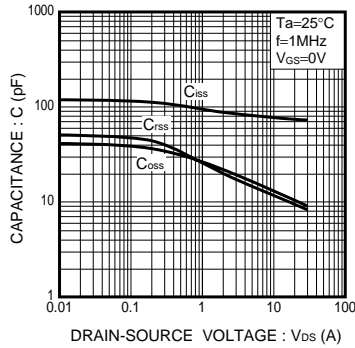


Fig.1 Typical Capacitance vs. Drain-Source Voltage

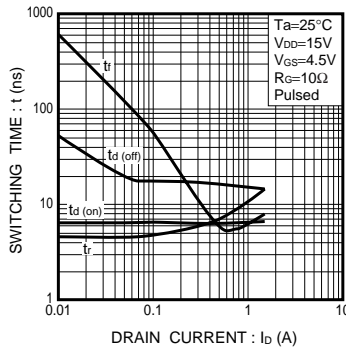


Fig.2 Switching Characteristics

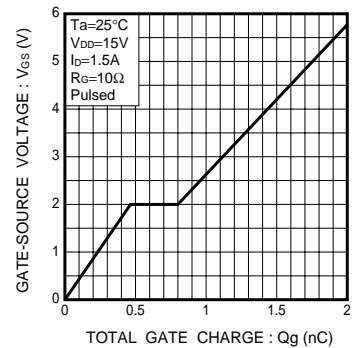


Fig.3 Dynamic Input Characteristics

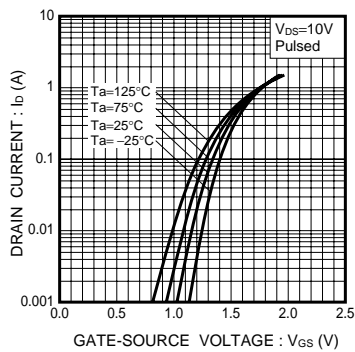


Fig.4 Typical Transfer Characteristics

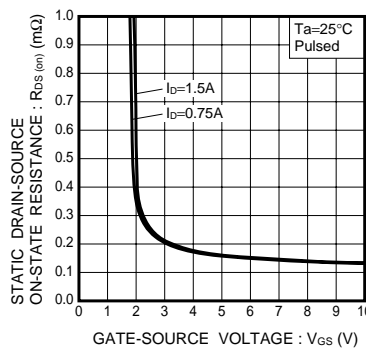


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

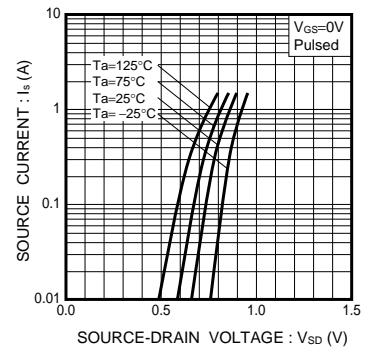


Fig.6 Source Current vs. Source-Drain Voltage

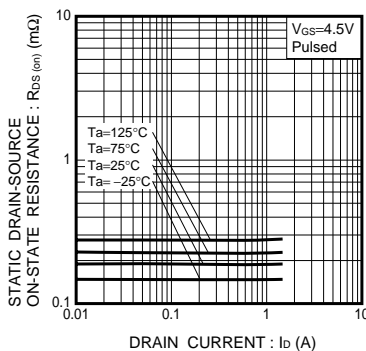


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

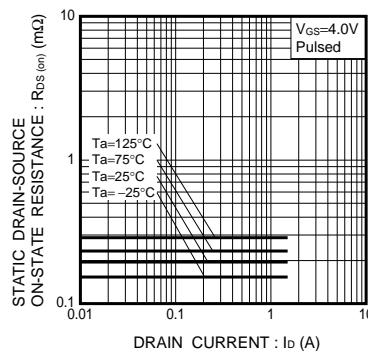


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

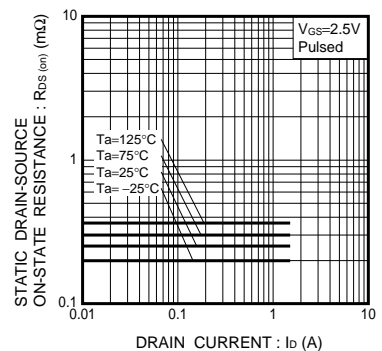


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

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●Electrical characteristic curves

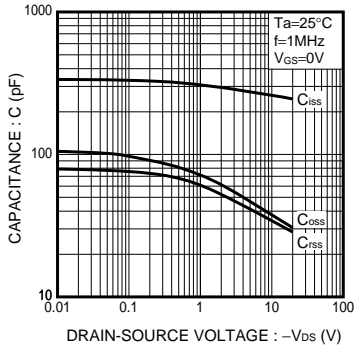


Fig.1 Typical Capacitance vs. Drain-Source Voltage

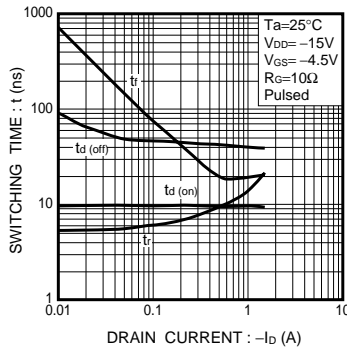


Fig.2 Switching Characteristics

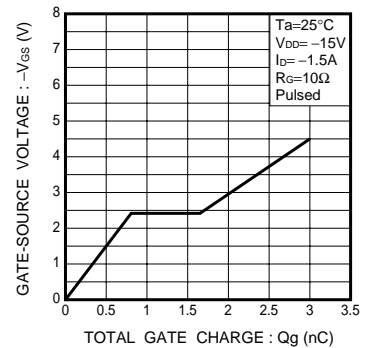


Fig.3 Dynamic Input Characteristics

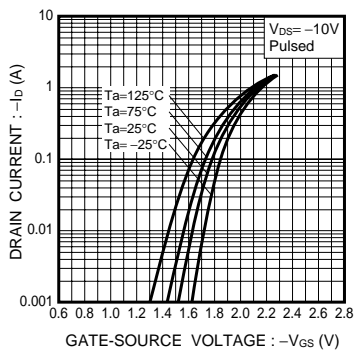


Fig.4 Typical Transfer Characteristics

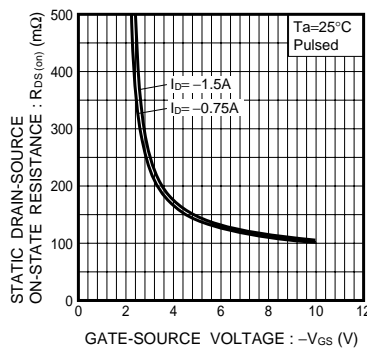


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

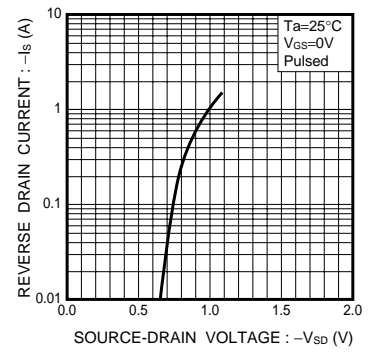


Fig.6 Source Current vs. Source-Drain Voltage

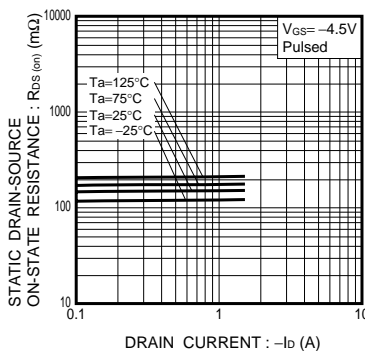


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

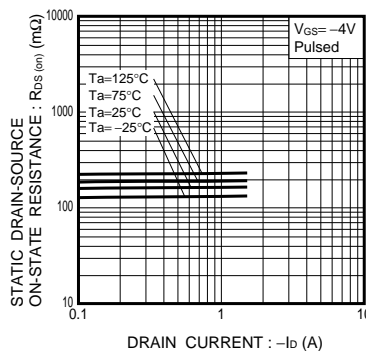


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

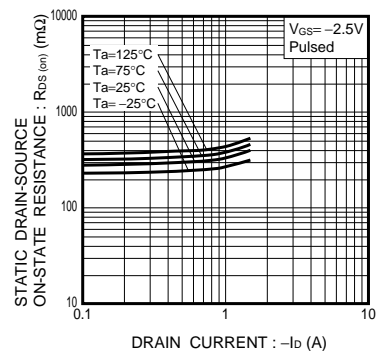


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

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●Measurement circuit

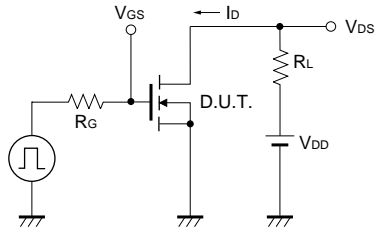


Fig.1-1 Switching Time Measurement Circuit

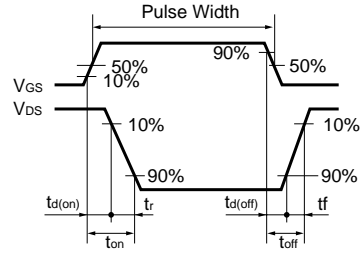


Fig.1-2 Switching Waveforms

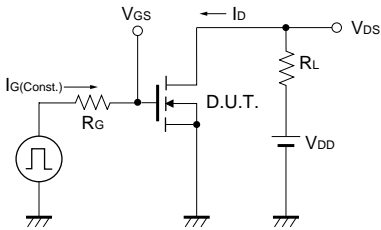


Fig.2-1 Gate Charge Measurement Circuit

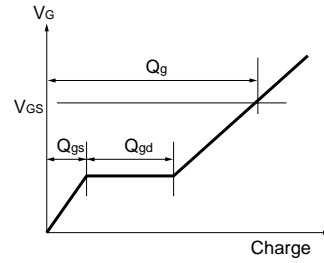


Fig.2-2 Gate Charge Waveform

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●Measurement circuit

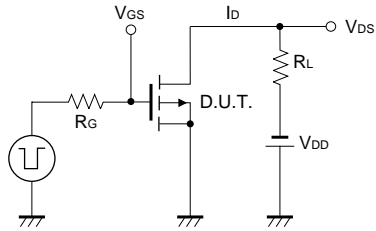


Fig.3-1 Switching Time Measurement Circuit

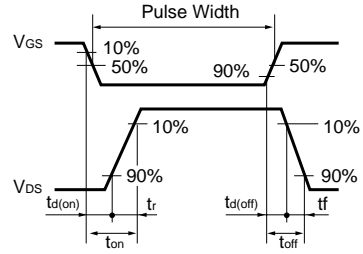


Fig.3-2 Switching Waveforms

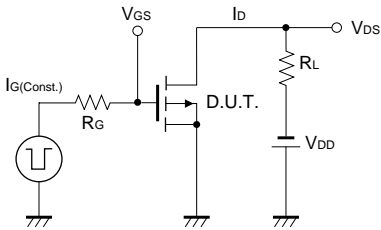


Fig.4-1 Gate Charge Measurement Circuit

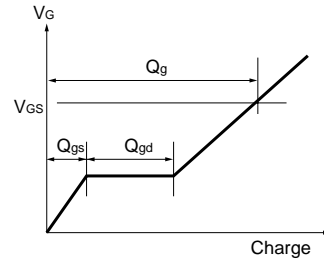


Fig.4-2 Gate Charge Waveform

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